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► To cite this version:

Steffi Woo, Fuhui Shao, Nianjheng Wu, Robert Schneider, Ashish Arora, et al.. Strain Relaxation and Excitonic Absorption of Atomically-Reconstructed WSe₂ Moiré Superlattices. Physical Sciences Symposium on Advanced Imaging and Spectroscopy for Nanoscale Materials, American Physical Society, Mar 2022, Chicago, United States. pp.2462-2463, 10.1017/S1431927622009424 . hal-04304699

HAL Id: hal-04304699

<https://hal.science/hal-04304699>

Submitted on 28 Nov 2023

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Strain Relaxation and Excitonic Absorption of Atomically-Reconstructed WSe₂ Moiré Superlattices

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Atomically-thin layers of semiconducting transition metal dichalcogenides (TMDs), namely tungsten diselenide (WSe₂), have attracted considerable interest because of new properties that can be obtained when artificially fabricated into van der Waals superlattices. Interlayer coupling is responsible for various properties, including the indirect-to-direct band gap cross-over from bulk and few-layered to monolayer TMDs. It has also been demonstrated that twist angle can be used to tune the interlayer coupling strength in bilayer MoS₂ [1] and WS₂ [2] homostructures. In this work, the high spatial and spectral resolution of monochromated electron energy-loss spectroscopy (EELS) coupled with four-dimensional scanning transmission electron microscopy (4D-STEM) in an aberration-corrected STEM are used to investigate the excitonic response of twisted bilayer WSe₂ with a low moiré angle and the strain relaxation of those that are atomically reconstructed.

Monolayered WSe₂ flakes were mechanically exfoliated from synthetic bulk crystals, and transferred onto SiO₂/Si wafers prior to assembly. The twisted bilayer WSe₂ structures were fabricated using a viscoelastic ‘tear and stack’ stamping method for controlled stacking and twist angle [3], before depositing onto a Quantifoil holey carbon TEM grid. Monochromated EELS and nano-beam electron diffraction with 1 mrad convergence angle were performed on a modified Nion HERMES-S200 (or ChromaTEM) operated at 60 kV with the sample cooled using liquid nitrogen (T ~ 150 K).

Well-defined hexagonal moiré patterns with nanometer periodicity are apparent for the low twist angles with high-resolution imaging. At twist angles below ~3°, some of the high-symmetry stacking regions become more energetically favorable, leading to an expansion of selected high-symmetry points into domains by atomic reconstruction. A low-angle annular dark-field (LAADF) image can be used to visualize the domain boundaries [4]. The domain boundary geometry has been demonstrated to differ between those of R-type (AA) and H-type (AA') stacking order in twisted TMDs that designates layers without and with inversion symmetry, respectively. R-type takes on a triangular geometry [Fig. 1(b,c)], while H-type resembles a kagome-like pattern [Fig. 1(d)]. 4D-STEM of the reconstructed bilayers reveals the nanoscale deformation that correlates perfectly with the location of the domain boundaries [Fig. 2]. The excitonic absorption signatures of these nanometric twisted bilayers [Fig. 1(e)] demonstrate a good general correspondence to the thickness dependence of the exciton resonances, namely a pronounced decrease in C exciton energy with the number of layers [5]. Comparing different twist angles in the bilayers also shows sizable blueshifts in the C exciton energy up to 200 meV, with extremes between the zero-twist and towards the anti-aligned (28°) case, indicating underlying differences in interlayer coupling with respect to the moiré angle.

Acknowledgements: The authors acknowledge funding from the ANR, program of future investment TEMPOS-CHROMATEM (No. ANR-10-EQPX- 50), and support by the European Union in the Horizon 2020 Framework Program (H2020-EU) under Grant Agreement No. 823717 (ESTEEM3).

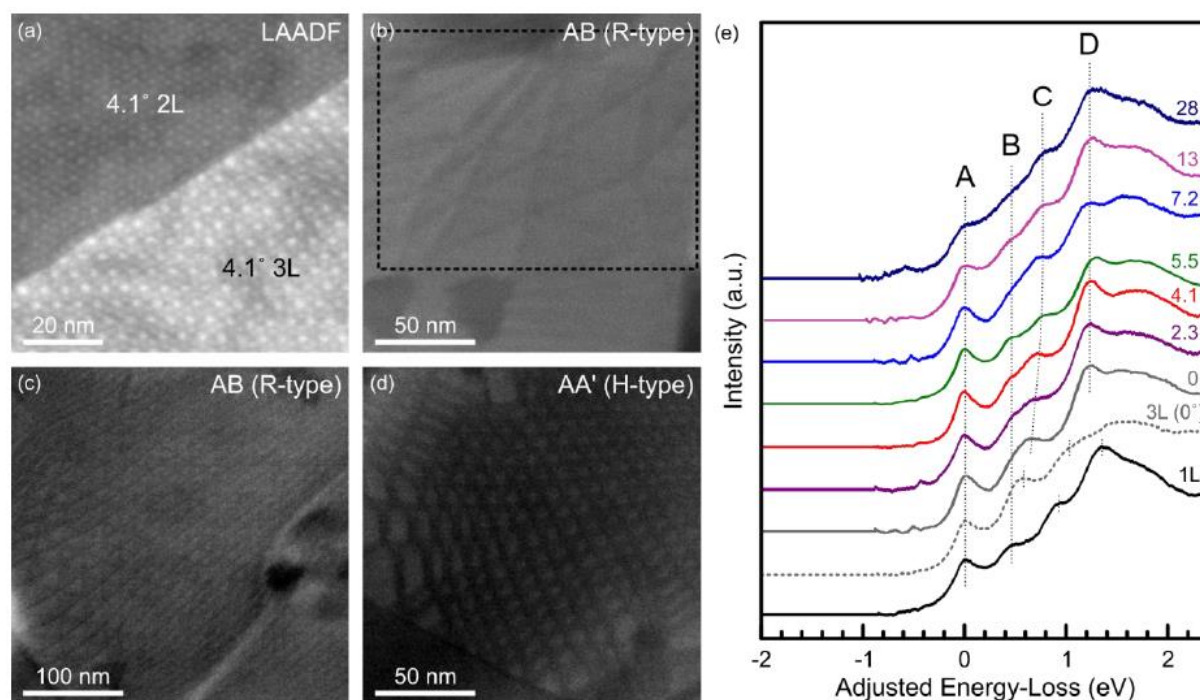


Figure 1. STEM-LAADF images of WSe₂ twisted bilayers (2Ls) with (a) 4.1° twist angle, and (b,c) AB (R-type) stacking, (d) AA' (H-type) stacking with atomic reconstruction. (e) Monochromated EELS spectra from twisted bilayers with various moiré angles compared to a representative monolayer (1L) and trilayer (3L) with zero twist. Spectra are offset in energy relative to the A exciton, and the dotted lines are to help guide the eye in the different exciton energy positions.

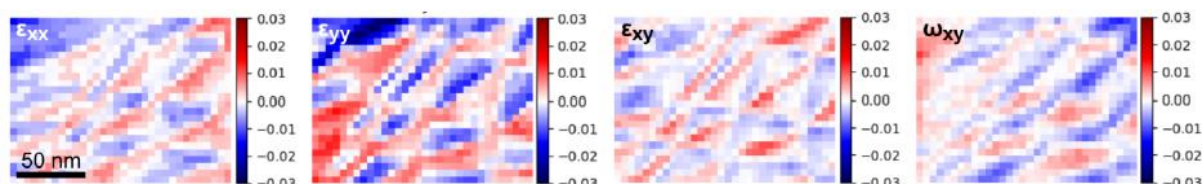


Figure 2. Strain maps obtained using 4D-STEM of the boxed region from Fig. 1(b), including axial strains, ϵ_{xx} , ϵ_{yy} , shear strain, ϵ_{xy} , and rotation ω_{xy} , showing strain relaxation corresponding to the distribution of alternating AB/BA domains, as a result of the atomic reconstruction.

References:

- [1] A. Castellanos-Gomez, H.S.J. van der Zant, & G.A. Steele, *Nano Research* **7**, 572–578 (2014).
- [2] W. Yan, L. Meng, Z. Meng, Y. Weng, L. Kang, L. and X. Li, *The Journal of Physical Chemistry C* **123**(50), 30684–30688 (2019).
- [3] K. Kim *et al.*, *Proceedings of the National Academy of Sciences* **114**(13), 3364–3369 (2017).
- [4] A. Weston, Y. Zou, Y., V. Enaldiev *et al.*, *Nature Nanotechnology* **15**, 592–597 (2020).
- [5] A. Arora, M. Koperski, K. Nogajewski *et al.*, *Nanoscale* **7**, 10421 (2015).